

isc Triacs

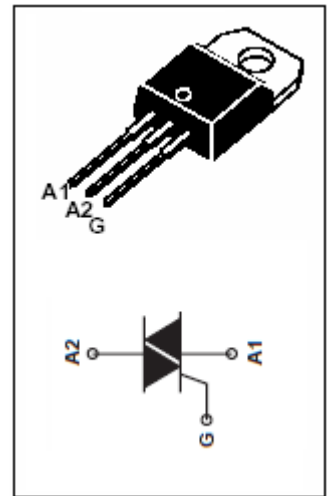
BTA08-600C

FEATURES

- With TO-220AB insulated package
- Suitable for general purpose applications where gate high sensitivity is required. Application on 4Q such as phase control and static switching.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	MIN	UNIT
V_{DRM}	Repetitive peak off-state voltage	600	V
V_{RRM}	Repetitive peak reverse voltage	600	V
$I_{T(RMS)}$	RMS on-state current (full sine wave) $T_j=105^\circ\text{C}$	8	A
I_{TSM}	Non-repetitive peak on-state current $t_p=20\text{ms}$	80	A
T_j	Operating junction temperature	110	°C
T_{stg}	Storage temperature	-45~150	°C
$R_{th(j-c)}$	Thermal resistance, junction to case	2.5	°C/W
$R_{th(j-a)}$	Thermal resistance, junction to ambient	60	°C/W

ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT	
I_{RRM}	Repetitive peak reverse current	$V_R=V_{RRM}$, $V_R=V_{RRM}$, $T_j=110^\circ\text{C}$	0.01 0.5	mA	
I_{DRM}	Repetitive peak off-state current	$V_D=V_{DRM}$, $V_D=V_{DRM}$, $T_j=110^\circ\text{C}$	0.01 0.5	mA	
I_{GT}	Gate trigger current	I	$V_D=12\text{V}$; $R_L=30\ \Omega$	25	mA
		II			
		III			
		IV			
I_H	Holding current	$I_{GT}=0.1\text{A}$, Gate Open	25	mA	
V_{GT}	Gate trigger voltage all quadrant	$V_D=12\text{V}$; $R_L=30\ \Omega$	1.3	V	
V_{TM}	On-state voltage	$I_T=11\text{A}$; $t_p=380\ \mu\text{s}$	1.55	V	